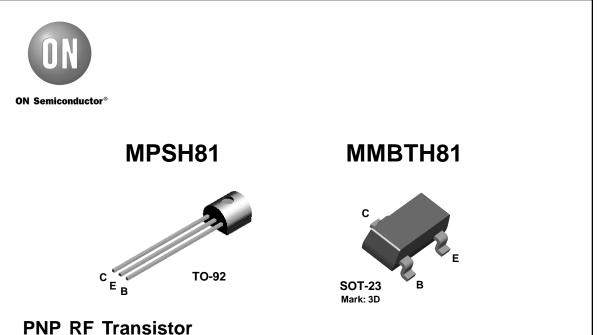
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This device is designed for general RF amplifier and mixer applications to 250 mHz with collector currents in the 1.0 mA to 30 mA range. Sourced from Process 75.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	20	V
V _{CBO}	Collector-Base Voltage	20	V
V _{EBO}	Emitter-Base Voltage	3.0	V
I _C	Collector Current - Continuous	50	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units	
		MPSH81	*MMBTH81		
P _D	Total Device Dissipation Derate above 25°C	350 2.8	225 1.8	mW mW/∘C	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125		°C/W	
$R_{ ext{ hetaJA}}$	Thermal Resistance, Junction to Ambient	357	556	°C/W	

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

PNP RF Transistor

(continued)

Electrical Characteristics TA = 25°C unless otherwise noted						
Symbol	Parameter	Test Conditions	Min	Max	Units	
OFF CHA	RACTERISTICS					
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 1.0 \text{ mA}, I_{\rm B} = 0$	20		V	
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 10 \ \mu {\rm A}, \ I_{\rm E} = 0$	20		V	
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{\rm E} = 10 \ \mu {\rm A}, \ I_{\rm C} = 0$	3.0		V	
I _{CBO}	Collector Cutoff Current	$V_{CB} = 10 \text{ V}, I_{E} = 0$		100	nA	
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 2.0 \text{ V}, I_{C} = 0$		100	nA	
ONCHAR	ACTERISTICS		•		-	
h _{FE}	DC Current Gain	$I_{C} = 5.0 \text{ mA}, V_{CE} = 10 \text{ V}$	60			
N/	Callester Exitter Caturation Valters			0.5	14	

h _{FE}	DC Current Gain	$I_{\rm C} = 5.0 \text{ mA}, V_{\rm CE} = 10 \text{ V}$	60		
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_{\rm C} = 5.0 \text{ mA}, I_{\rm B} = 0.5 \text{ mA}$		0.5	V
V _{BE(on)}	Base-Emitter On Voltage	$I_{C} = 5.0 \text{ mA}, V_{CE} = 10 \text{ V}$		0.9	V

SMALL SIGNAL CHARACTERISTICS

f _T	Current Gain - Bandwidth Product	$I_{C} = 5.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 100 MHz	600		MHz
C _{cb}	Collector-Base Capacitance	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$		0.85	pF
C _{ce}	Collector Emitter Capcitance	$V_{CB} = 10 \text{ V}, I_B = 0, f = 1.0 \text{ MHz}$		0.65	pF

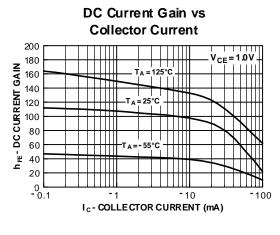
*Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

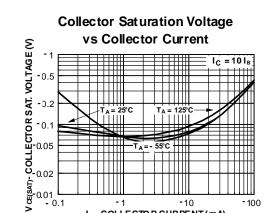
 $\ensuremath{\textbf{NOTE:}}$ All voltages (V) and currents (A) are negative polarity for PNP transistors.

Spice Model

PNP(Is=10f Xti=3 Eg=1.11 Vaf=100 Bf=133.8 Ise=1.678p Ne=2.159 Ikf=.1658 Nk=.901 Xtb=1.5 Var=100 Br=1 Isc=9.519n Nc=3.88 Ikr=5.813 Rc=7.838 Cjc=2.81p Mjc=.1615 Vjc=.8282 Fc=.5 Cje=2.695p Mje=.3214 Vje=.7026 Tr=11.32n Tf=97.83p Itf=69.29 Xtf=599u Vtf=10)

Typical Characteristics





I c- COLLECTOR CURRENT (mA)

MPSH81 / MMBTH81 **PNP RF Transistor** (continued) **Typical Characteristics** (continued) Base-Emitter ON Voltage **Base-Emitter Saturation NOLTAGE (V)** vs Collector Current Voltage vs Collector Current V BEOM)- BASE-EMITTER ON VOLTAGE (V) 0.0 7.0 8.0 8.0 7.0 8.0 8.0 8.0 V_{CE}= 10V $I_{\rm C} = 10 I_{\rm B}$ T_A = 25°C **H** -1.2 Ф - **BASE-EMITTER** -0.8 -0.9 T_A = 100°C 1111 а-(_{мс})-04 -0-04 Л = 125 0 - 0.1 **-**0.1 -100 -1 -10 I^C- COLLECTOR CURRENT (mA) -10 -100 Ic - COLLECTOR CURRENT (mA) Input / Output Capacitance **Collector Reverse Current** I ces- COLLECTOR REVERSE CURRENT (IA) vs Ambient Temperature vs Reverse Bias Voltage 3 100 = 1.0 MHz 2.8 10 V_{CE}=-6.0V Cobo V_{CE}=-3.0V 0.1 1.4 Ċibo 1.2 1 25 50 75 100 150 125 0 -2 -4 -6 -8 -10 T_A - AMBIENT TEMPERATURE (°C) **REVERSE BIAS VOLTAGE (V) Contours of Constant Gain Power Dissipation vs** Ambient Temperature Bandwidth Product (f_T) 350 TO-92 -8 SOT-23 1500 MHz 1200 MH -6 500 MHz 200 MH -2 500 MHz 200 MH 900 MHz _ ل_ - 0.1 0 -10 -100 - 1 50 75 100 TEMPERATURE (°C) 0 25 125 150 Ic- COLLECTOR CURRENT (mA)

